



Shantou Huashan Electronic Devices Co.,Ltd.

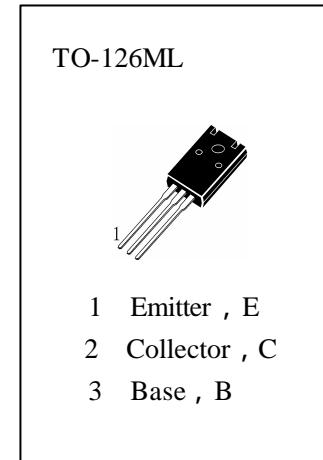
NPN SILICON TRANSISTOR

H882**APPLICATIONS**

Audio Frequency Power Amplifier , Switching Power Amplifier.

ABSOLUTE MAXIMUM RATINGS (T_a=25)

T _{stg}	Storage Temperature.....	-55~150
T _j	Junction Temperature.....	150
P _C	Collector Dissipation (T _c =25)	10W
P _C	Collector Dissipation (T _A =25)	1W
V _{CBO}	Collector-Base Voltage	40V
V _{CEO}	Collector-Emitter Voltage.....	30V
V _{EBO}	Emitter-Base Voltage.....	5V
I _C	Collector Current (DC)	3A
I _b	Base Current (DC)	0.6A

**ELECTRICAL CHARACTERISTICS (T_a=25)**

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
I _{CBO}	Collector-Base Cutoff Current			1	μA	V _{CB} =30V, I _E =0
I _{EBO}	Emitter- Base Cutoff Current			1	μA	V _{EB} =5V, I _C =0
h _{FE}	DC Current Gain	60		400		V _{CE} =-2V, I _C =1A
V _{CE (sat)}	Collector- Emitter Saturation Voltage		0.3	0.5	V	I _C =2A, I _B =-0.2A
V _{BE (sat)}	Base -Emitter Saturation Voltage		1.0	2.0	V	I _C =2A, I _B =0.2A
C _{ob}	Output Capacitance		45		pF	V _{CB} =10V , I _E =0 , f=1MHz
f _T	Current Gain-Bandwidth Product		90		MHz	V _{CE} =5V , I _E =0.1A

h_{FE} Classification

R	0	Y	G
60—120	100—200	160—320	200—400



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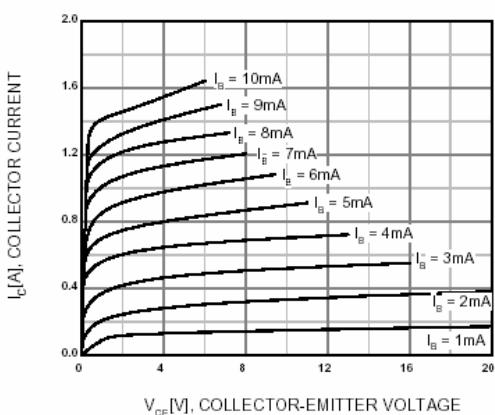


Figure 1. Static Characteristic

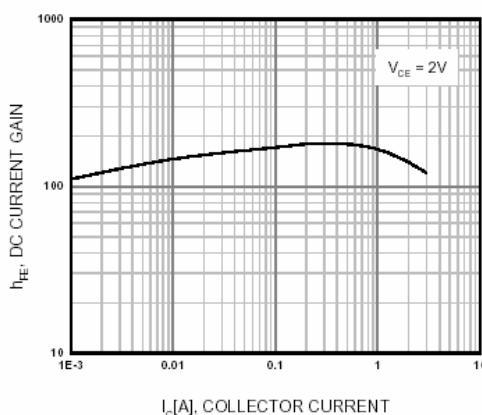


Figure 2. DC current Gain

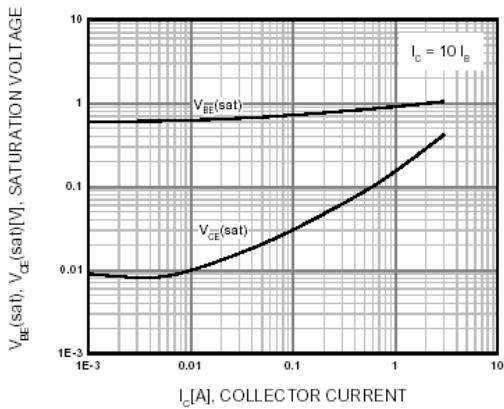


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

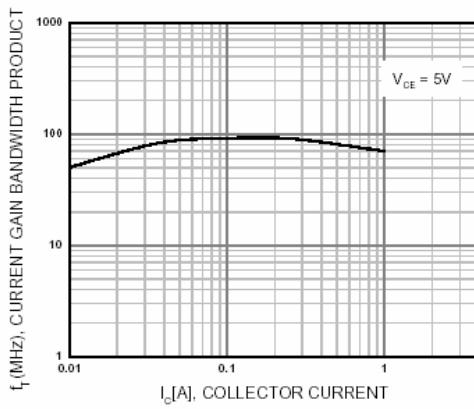


Figure 4. Current Gain Bandwidth Product

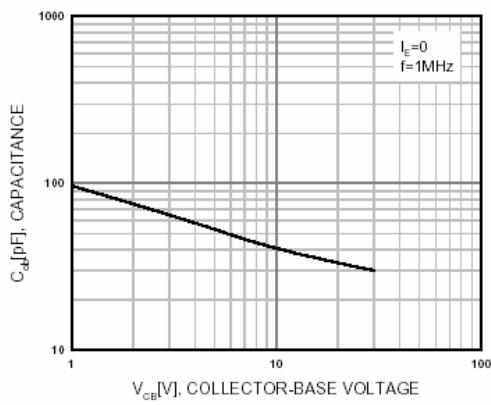


Figure 5. Collector Output Capacitance

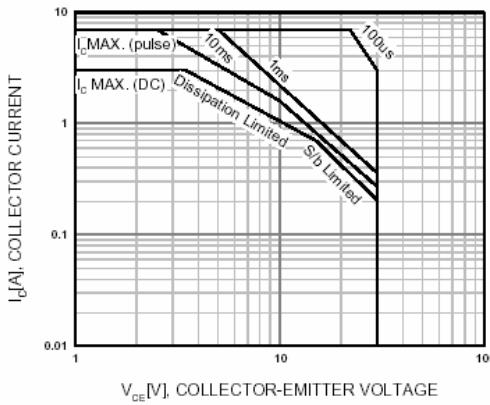


Figure 6. Safe Operating Area



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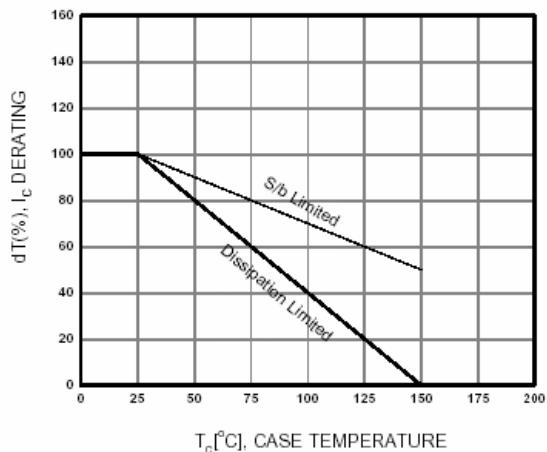


Figure 7. Derating Curve Of Safe Operating Areas

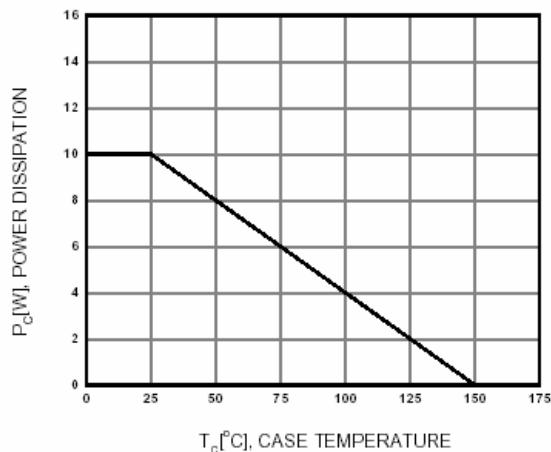


Figure 8. Power Derating